



ACE2301B

P-Channel Enhancement Mode MOSFET

Description

ACE2301B is produced with high cell density DMOS trench technology, which is especially used to minimize on-state resistance. This device particularly suits low voltage applications such as portable equipment, power management and other battery powered circuits, and low in-line power dissipation are needed in a very small outline surface mount package with excellent thermal and electrical capabilities.

Features

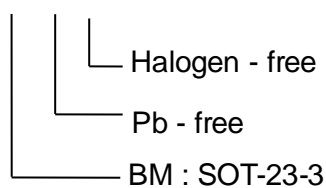
- $V_{DS}=-20V$, $V_{GS} 8V$, $I_D=-2.3A$
- $R_{DS(ON)}$ @ $V_{GS}=-4.5V/I_D -2.8A$, 100mR(Typ.)
- $R_{DS(ON)}$ @ $V_{GS}=-2.5V/I_D -2A$, 120mR(Typ.)

Absolute Maximum Ratings

Parameter	Symbol	Max	Unit
Drain-Source Voltage	V_{DSS}	-20	V
Gate-Source Voltage	V_{GSS}	± 8	V
Drain Current	Continuous	-2.3	A
	Pulsed ⁽¹⁾	-10	
Power Dissipation	25°C	750	mW
	70°C	480	
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C

Ordering information

ACE2301B XX + H





ACE2301B

P-Channel Enhancement Mode MOSFET

Notes

ACE does not assume any responsibility for use as critical components in life support devices or systems without the express written approval of the president and general counsel of ACE Technology Co., LTD. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ACE Technology Co., LTD.
<http://www.ace-ele.com/>